

NCE P-Channel Super Trench Power MOSFET

Description

The NCEP40P60Q uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification

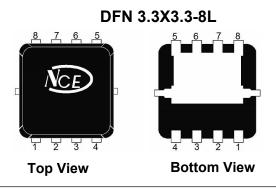
Application

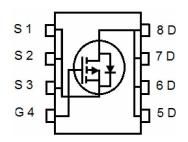
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =-40V, I_{D} =-60A $R_{DS(ON)}$ =8.8mΩ (typical) @ V_{GS} =-10V $R_{DS(ON)}$ =12.5mΩ (typical) @ V_{GS} =-4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40P60Q	NCEP40P60Q	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D (T _C =25°C)	-60	А
Drain Current-Continuous(T _C =100℃)	I _D (T _C =100°C)	-42	А
Pulsed Drain Current	I _{DM}	-240	А
Maximum Power Dissipation(T _C =25°ℂ)	P _D (T _C =25°C)	75	W
Pulsed Drain Current	I _{DM}	-240	А
Derating factor		0.6	W/℃
Single pulse avalanche energy (Note 1)	E _{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R _{eJC}	1.67	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Tym	Max	Unit
	Symbol	Condition	IVIIII	Тур	IVIAX	Unit
Off Characteristics		T		1	ı	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.1	-1.7	-2.2	V
Dunin Course On Ctata Basistana	_	V _{GS} =-10V, I _D =-20A	-	8.8	11	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	12.5	17.0	mΩ
Forward Transconductance	G FS	V _{DS} =-5V,I _D =-20A	-	30	-	S
Dynamic Characteristics						
Input Capacitance	C _{lss}	\/ 00\/\/ 0\/	-	2450	-	PF
Output Capacitance	Coss	V _{DS} =-20V,V _{GS} =0V,	-	660	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	18	-	PF
Switching Characteristics (Note 2)		,	•			
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V _{DD} =-20V,I _D =-20A	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =-10V,R _G =1.6Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg	.,	-	39	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-20V, I_{D} =-20A,	-	7.8		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	5.3		nC
Drain-Source Diode Characteristics		ı		1	1	1
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =-20A	-		-1.2	V
Diode Forward Current	Is		-	-	-60	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A	-	22		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	58		nC
	1	<u> </u>		1	l	

Notes:

^{1.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=-20V,VG=-10V,L=0.5mH,Rg=25 Ω

^{2.} Guaranteed by design, not subject to production

^{3.} These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=150°C. The SOA curve provides a single pulse rating.



Typical Electrical and Thermal Characteristics

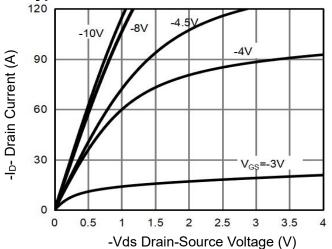


Figure 1 Output Characteristics

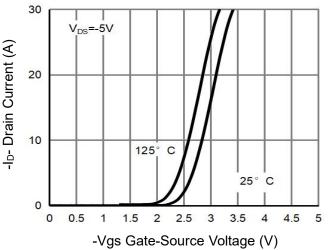


Figure 2 Transfer Characteristics

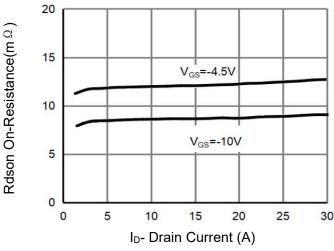


Figure 3 Rdson- Drain Current

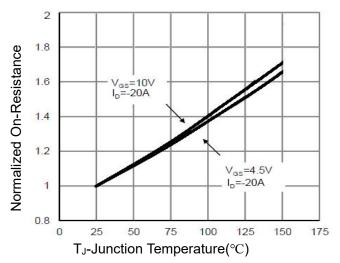


Figure 4 Rdson-JunctionTemperature

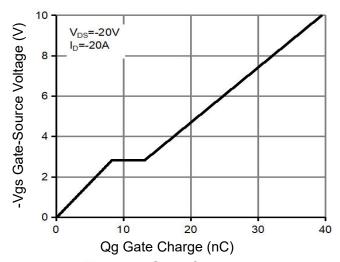


Figure 5 Gate Charge

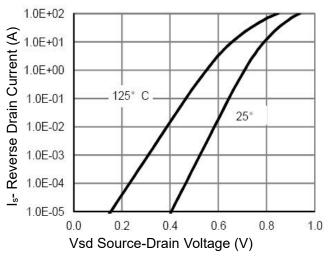


Figure 6 Source- Drain Diode Forward



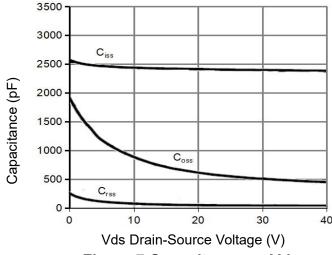


Figure 7 Capacitance vs Vds

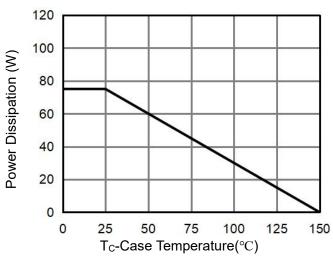


Figure 9 Power De-rating

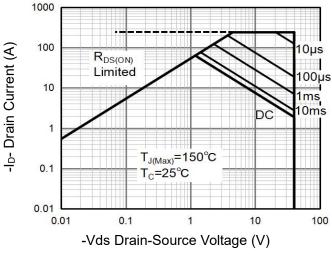


Figure 8 Safe Operation Area (Note 3)

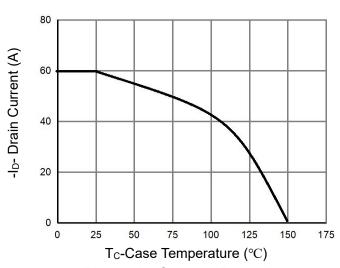


Figure 10 Current De-rating

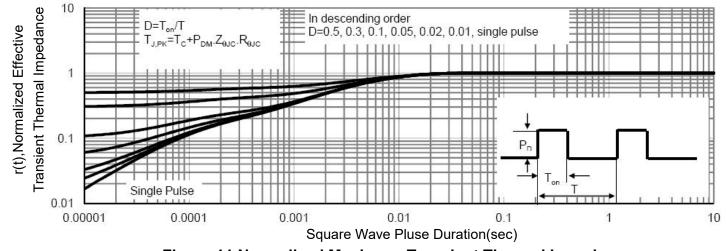
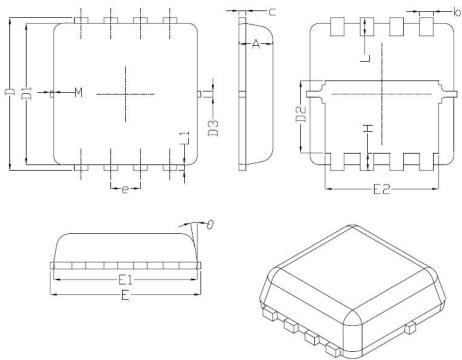


Figure 11 Normalized Maximum Transient Thermal Impedance



DFN3.3X3.3-8L Package Information



Comphal	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
A	0.70	0.75	0.80		
b	0.25	0.30	0.35		
С	0.10	0.15	0.25		
D	3.25	3.35	3.45		
D1	3.00	3.10	3.20		
D2	1.48	1.58	1.68		
D3	-	0.13	-		
E	3.20	3.30	3.40		
E1	3.00	3.15	3.20		
E2	2.39	2.49	2.59		
е	0.65BSC				
Н	0.30	0.39	0.50		
L	0.30	0.40	0.50		
L1	-	0.13	-		
M	*	*	0.15		
θ		10°	12 [°]		

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NCEP40P60Q

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